

SOT89 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

FCX491

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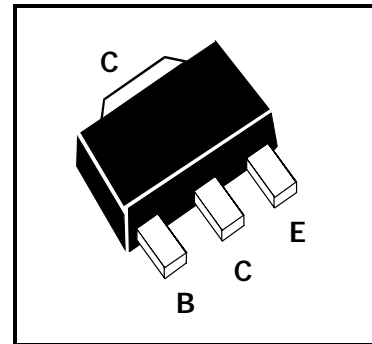


FEATURES

- * 60 Volt V_{CEO}
- * 1 Amp continuous current
- * $P_{tot} = 1$ Watt

COMPLEMENTARY TYPE – FCX591

PARTMARKING DETAIL – N1



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	80		V	$I_C=100\mu\text{A}$
	$V_{CEO(sus)}$	60		V	$I_C=10\text{mA}^*$
	$V_{(BR)EBO}$	5		V	$I_E=100\mu\text{A}$
Collector Cut-Off Currents	I_{CBO}		100	nA	$V_{CB}=60\text{V}$,
	I_{CES}		100	nA	$V_{CE}=60\text{V}$
Emitter Cut-Off Current	I_{EBO}		100	nA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	$I_C=500\text{mA}$, $I_B=50\text{mA}^*$ $I_C=1\text{A}$, $I_B=100\text{mA}^*$
			0.50	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.1	V	$I_C=1\text{A}$, $I_B=100\text{mA}^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		1.0	V	$I_C=1\text{A}$, $V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	100	300		$I_C=1\text{mA}$, $V_{CE}=5\text{V}$ $I_C=500\text{mA}$, $V_{CE}=5\text{V}^*$ $I_C=1\text{A}$, $V_{CE}=5\text{V}^*$ $I_C=2\text{A}$, $V_{CE}=5\text{V}^*$
		100			
		80			
		30			
Transition Frequency	f_T	150		MHz	$I_C=50\text{mA}$, $V_{CE}=10\text{V}$ $f=100\text{MHz}$
Collector-Base Breakdown Voltage	C_{obo}		10	pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical Characteristics graphs see FMMT491 datasheet